

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions and listings of claims in the application:

1-19. (Canceled)

20. (Original) A method for protecting a complementary metal-oxide semiconductor device from electrostatic discharge, comprising:

providing a bi-directional silicon controlled rectifier in the complementary metal-oxide semiconductor circuit;

isolating the bi-directional silicon controlled rectifier from a substrate of the complementary metal-oxide semiconductor circuit;

providing a signal pad coupled to the bi-directional silicon controlled rectifier for receiving an electrostatic discharge; and

protecting the device from the electrostatic discharge with the bi-directional silicon controlled rectifier.

21. (Original) The method as claimed in claim 20, wherein the electrostatic discharge is a positive discharge.

22. (Original) The method as claimed in claim 20, wherein the electrostatic discharge is a negative discharge.

23. (Original) The method as claimed in claim 20, wherein the step of isolating the bi-directional silicon controlled rectifier from a substrate of the complementary metal-oxide semiconductor circuit includes a step of providing an insulator layer between the substrate and the bi-directional silicon controlled rectifier.

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24. (Original) The method as claimed in claim 23, further comprising a step of forming the bi-directional silicon controlled rectifier in a layer of silicon.

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